

# MBN1200E17D

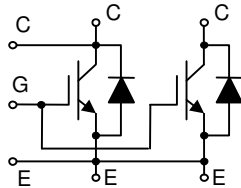
PRELIMINARY SPEC.

Silicon N-channel IGBT

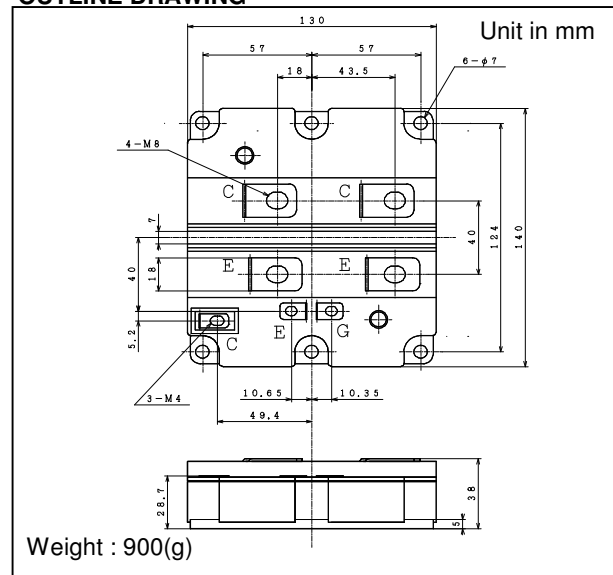
## FEATURES

- \* High speed, low loss IGBT module.
- \* Low driving power due to low input capacitance MOS gate.
- \* Low noise due to ultra soft fast recovery diode.
- \* High reliability, high durability module.
- \* High thermal fatigue durability.  
( $\Delta T_c=70^\circ\text{C}$ ,  $N>30,000$ cycles)
- \* Isolated heat sink (terminal to base).

## CIRCUIT DIAGRAM



## OUTLINE DRAWING



## ABSOLUTE MAXIMUM RATINGS ( $T_c=25^\circ\text{C}$ )

Item	Symbol	Unit	MBN1200E17D
Collector Emitter Voltage	$V_{CES}$	V	1,700
Gate Emitter Voltage	$V_{GES}$	V	$\pm 20$
Collector Current	DC	$I_C$	1,200
	1ms	$I_{CP}$	2,400
Forward Current	DC	$I_F$	1,200
	1ms	$I_{FM}$	2,400
Junction Temperature	$T_j$	$^\circ\text{C}$	-40 ~ +125
Storage Temperature	$T_{stg}$	$^\circ\text{C}$	-40 ~ +125
Isolation Voltage	$V_{ISO}$	$V_{RMS}$	4,000(AC 1 minute)
Screw Torque	Terminals (M4/M8)	-	2/10 (1)
	Mounting (M6)	-	6 (2)

Notes: (1) Recommended Value  $1.8\pm 0.2/9\pm 1\text{N}\cdot\text{m}$ (2) Recommended Value  $5.5\pm 0.5\text{N}\cdot\text{m}$ 

## ELECTRICAL CHARACTERISTICS

Item	Symbol	Unit	Min.	Typ.	Max.	Test Conditions
Collector Emitter Cut-Off Current	$I_{CES}$	mA	-	-	10	$V_{CE}=1,700\text{V}$ , $V_{GE}=0\text{V}$ , $T_j=25^\circ\text{C}$
			-	10	35	$V_{CE}=1,700\text{V}$ , $V_{GE}=0\text{V}$ , $T_j=125^\circ\text{C}$
Gate Emitter Leakage Current	$I_{GES}$	nA	-500	-	+500	$V_{GE}=\pm 20\text{V}$ , $V_{CE}=0\text{V}$ , $T_j=25^\circ\text{C}$
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	V	-	2.7	3.3	$I_C=1,200\text{A}$ , $V_{GE}=15\text{V}$ , $T_j=125^\circ\text{C}$
Gate Emitter Threshold Voltage	$V_{GE(TH)}$	V	5.0	6.5	8.0	$V_{CE}=10\text{V}$ , $I_C=120\text{mA}$ , $T_j=25^\circ\text{C}$
Input Capacitance	$C_{ies}$	nF	-	100	-	$V_{CE}=10\text{V}$ , $V_{GE}=0\text{V}$ , $f=100\text{kHz}$ , $T_j=25^\circ\text{C}$
Internal Gate Resistance	$R_{ge}$	$\Omega$	-	0.8	-	$V_{CE}=10\text{V}$ , $V_{GE}=0\text{V}$ , $f=100\text{kHz}$ , $T_j=25^\circ\text{C}$
Switching Times	Rise Time	$t_r$	-	0.6	1.0	$V_{CC}=900\text{V}$ , $I_C=1,200\text{A}$ $L=65\text{nH}$ , $C_{GE}=120\text{nF}$ (TBD) (3) $R_G=1.5\Omega$ (TBD) (3) $V_{GE}=\pm 15\text{V}$ , $T_j=125^\circ\text{C}$
	Turn On Time	$t_{on}$	-	0.9	1.8	
	Fall Time	$t_f$	-	0.3	0.7	
	Turn Off Time	$t_{off}$	-	1.4	3.4	
Peak Forward Voltage Drop	$V_{FM}$	V	-	1.9	2.5	$I_F=1,200\text{A}$ , $V_{GE}=0\text{V}$ , $T_j=125^\circ\text{C}$
Reverse Recovery Time	$t_{rr}$	$\mu\text{s}$	-	0.5	1.0	$V_{CC}=900\text{V}$ , $I_F=1,200\text{A}$
Turn On Loss	$E_{on(10\%)}$	J/P	-	0.25	0.4	$L=65\text{nH}$ , $C_{GE}=120\text{nF}$ (TBD) (3)
Turn Off Loss	$E_{off(10\%)}$	J/P	-	0.35	0.5	$R_G=1.5\Omega$ (TBD) (3)
Reverse Recovery Loss	$E_{rr(10\%)}$	J/P	-	0.4	0.6	$V_{GE}=\pm 15\text{V}$ , $T_j=125^\circ\text{C}$
Stray inductance module	$L_{SCE}$	nH	-	18	-	
Thermal Impedance	IGBT	$R_{th(j-c)}$	-	-	0.018	Junction to case
	FWD	$R_{th(j-c)}$	-	-	0.030	
Contact Thermal Impedance	$R_{th(c-f)}$	K/W	-	0.008	-	Case to fin

Notes:(3)  $R_G$  and  $C_{GE}$  value is the test condition's value for evaluation of the switching times, not recommended value.Please, determine the suitable  $R_G$  and  $C_{GE}$  value after the measurement of switching waveforms (overshoot voltage, etc.) with appliance mounted.

\* Please contact our representatives at order.

\* For improvement, specifications are subject to change without notice.

\* For actual application, please confirm this spec sheet is the newest revision.

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